

Contents

PREFACE	xi
ACKNOWLEDGMENTS	xiii
MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS	xiv

PART I: FUNDAMENTALS OF ION-MATERIAL INTERACTIONS

DYNAMIC MONTE CARLO SIMULATION OF ION BEAM AND PLASMA TECHNIQUES W. Möller	3
*SIMULATIONS OF LOW-ENERGY ION/SURFACE INTERACTION EFFECTS DURING EPITAXIAL FILM GROWTH Makoto Kitabatake and J.E. Greene	9
LOW ENERGY Ar ION BOMBARDMENT OF (001) Si: DEFECTS AND SURFACE MORPHOLOGY M.V.R. Murty and Harry A. Atwater	21
MOLECULAR DYNAMICS SIMULATIONS OF THIN FILM DIAMOND GROWTH Bernard A. Pailthorpe and Peter Knight	29
MOLECULAR DYNAMICS SIMULATIONS OF ION BEAM MIXING A.M. Mazzone	35
UNIVERSAL ENERGY DEPENDENCE OF SPUTTERING YIELDS AT LOW ION ENERGY J. Muri and Ch. Steinbrüchel	41
EXPERIMENTAL AND THEORETICAL INVESTIGATIONS ON THE INTERRELATION OF CHARGE EXCHANGE PROCESSES AND ENERGY LOSS OF PARTICLES AT METAL SURFACES A. Närmann, W. Heiland, R. Monreal, F. Flores, and P.M. Echenique	47
ISLAND EVOLUTION DURING EARLY STAGES OF ION-ASSISTED FILM GROWTH: Ge ON SiO ₂ Shouleh Nikzad and Harry A. Atwater	53
ION/NEUTRAL BEAM ASSISTED ETCHING OF SEMICONDUCTORS: CHEMICAL MODIFICATIONS OF THE ADSORBED PHASE Glenn C. Tyrrell, Duncan Marshall, and Richard B. Jackman	61

*Invited Paper

PART II: MICROWAVE ION SOURCES
FOR DEPOSITION AND ETCHING

PROPERTIES OF SiO ₂ FILMS FABRICATED BY MICROWAVE ECR PLASMA PROCESSING WITH AND WITHOUT ENERGETIC PARTICLE BOMBARDMENT DURING FILM DEPOSITION PART I. FABRICATION PROCESSES AND PHYSICAL PROPERTIES T.T. Chau, S.R. Mejia, and K.C. Kao	69
STRUCTURAL AND INTERFACIAL CHARACTERISTICS OF THIN (<10 nm) SiO ₂ FILMS GROWN BY ELECTRON CYCLOTRON RESONANCE PLASMA OXIDATION ON [100] Si SUBSTRATES Tai D. Nguyen, D.A. Carl, D.W. Hess, M.A. Lieberman, and R. Gronsky	75
*CUBIC BORON NITRIDE PREPARED BY AN ECR PLASMA Y. Osaka, M. Okamoto, and Y. Utsumi	81
THE ECR-PLASMA DEPOSITION OF SILICON NITRIDE ON A TUNNEL OXIDE J.C. Barbour, H.J. Stein, and C.A. Outten	91
*ECR PLASMA ETCHING TECHNOLOGY FOR ULSIs Seiji Samukawa	97
THE MECHANISMS OF REACTIVE ION ETCHING OF SiO _x (x<2) WITH ELECTRON CYCLOTRON RESONANCE AND KAUFMAN ION SOURCES R.A. Kant, C.R. Eddy, Jr., and B.D. Sartwell	109
SHALLOW P ⁺ -N JUNCTION FABRICATION BY PLASMA IMMERSION ION IMPLANTATION C.A. Pico, X.Y. Qian, E. Jones, M.A. Lieberman, and N.W. Cheung	115
ELECTRON CYCLOTRON RESONANCE HYDROGENATION OF POLY-Si THIN FILM TRANSISTORS ON SiO ₂ /Si SUBSTRATES Gand Liu, Robert A. Ditzio, Stephen J. Fonash, and Nang Tran	121
ELECTRON CYCLOTRON RESONANCE HYDROGEN PLASMA INDUCED DEFECTS IN THERMALLY GROWN AND SPUTTER DEPOSITED SiO ₂ W.L. Hallett, R.A. Ditzio, and S.J. Fonash	127

PART III: PROCESSING OF HIGH-T_c
THIN FILMS AND INTERFACES

*THIN FILM GROWTH OF HIGH T _c SUPERCONDUCTORS BY MICRO-WAVE PLASMA ASSISTED REACTIVE EVAPORATION Akira Tsukamoto, Masahiko Hiratani, Toshiyuki Aida, Yoshinobu Tarutani, and Kazumasa Takagi	135
CRYSTALLINE ORIENTATION CONTROL IN Bi-Sr-Ca-Cu-O THIN FILMS Yoshiki Ishizuka, Yoshiaki Terashima, and Tadao Miura	147
*Invited Paper	

STUDY OF THE ORIENTATION OF $YBa_2Cu_3O_{7-x}$ THIN FILMS IN-SITU PREPARED BY REACTIVE COEVAPORATION WITH RF ACTIVATED OXYGEN-OZONE PLASMA	153
M. Nagata, H. Nojima, H. Shintaku, and M. Koba	
PREPARATION OF OPTICALLY SMOOTH SURFACES OF HIGH- T_c SUPERCONDUCTING FILMS	159
J.H. Kim, A. Kapitulnik, J.S. Harris, Jr., K. Char, I. Bozovic, and W.Y. Lee	
PLASMA OXIDATION OF Y-Ba-Cu-O PRECURSOR FILAMENTS	165
J.D. Klein, J.P. Hachey, and A. Yen	
ENERGY DISTRIBUTION OF NEGATIVE OXYGEN IONS EMITTED FROM YBaCuO AND IRON GARNET TARGETS BY dc- AND rf- MAGNETRON SPUTTERING	171
Jens-Peter Krumme, Ron A.A. Hack, and Ivo J.M.M. Raaijmakers	
PART IV: ELECTRONIC MATERIALS: III-V COMPOUNDS	
*GaAs EPITAXIAL GROWTH BY ECR-MBE	179
Naoto Kondo, Yasushi Nanishi, Tomohiro Shibata, Norio Yamamoto, and Masatomo Fujimoto	
$CH_4:H_2:Ar$ rf/ECR PLASMA ETCHING OF GaAs AND InP	191
Victor J. Law, S.G. Ingram, G.A.C. Jones, R.C. Grimwood, and H. Royal	
STRUCTURAL AND COMPOSITIONAL MODIFICATIONS OF III-V TERNARY AND QUATERNARY COMPOUNDS INDUCED BY ION BOMBARDMENT	197
A. di Bona, A. Facchini, S. Valeri, G. Ottaviani, and A. Piccirillo	
PERSISTENT PHOTOCONDUCTIVITY AND THERMAL RECOVERY KINETICS OF LOW ENERGY Ar^+ BOMBARDED GaAs	203
A. Vaseashta and L.C. Burton	
ELECTRICAL DAMAGE DUE TO LOW ENERGY PLASMA PROCESSING OF GaAs STRUCTURES	209
Hans P. Zappe and Gudrun Kaufel	
CHEMICAL PRECURSORS FOR GaAs ETCHING WITH LOW ENERGY ION BEAMS: CHLORINE ADSORPTION ON GaAs(100)	215
Richard B. Jackman, Glenn C. Tyrrell, Duncan Marshall, Catherine L. French, and John S. Foord	
PART V: ELECTRONIC MATERIALS: SILICON AND Si-Ge	
HETEROEPITAXY OF Si/Si $_{1-x}$ Ge $_x$ GROWN BY REMOTE PLASMA- ENHANCED CHEMICAL VAPOR DEPOSITION	223
T. Hsu, R. Qian, D. Kinosky, J. Irby, B. Anthony, S. Banerjee, A. Tasch, and C. Magee	

*Invited Paper

EVIDENCE OF OSCILLATING OXIDE GROWTH MECHANISM DURING OXYGEN PLASMA OXIDATION OF SILICON Son Nguyen, Tue Nguyen, D. Dobuzinsky, R. Gleason, and M. Gibson	229
ROOM TEMPERATURE NITRIDATION AND OXIDATION OF Si, Ge AND MBE-GROWN SiGe USING LOW ENERGY ION BEAMS (0.1 - 1 keV) O. Vancauwenberghe, O.C. Hellman, N. Herbots, J.L. Olson, W.J. Tan, and W.J. Croft	235
ATOMIC HYDROGEN PASSIVATION OF HIGH ENERGY HYDROGEN IMPLANTS K. Srikanth, J. Shenal, and S. Ashok	241
THE ROLE OF OXYGEN IN THE CF ₂ Cl ₂ REACTIVE ION ETCHING OF PECVD FILMS Yue Kuo	249
THE INFLUENCE OF HBr DISCHARGE AMBIENCE ON POLY-Si/SiO ₂ ETCHING SELECTIVITY E. Ikawa, K. Tokashiki, T. Kikkawa, Y. Teraoka, and I. Nishiyama	255
PART VI: ION PROCESSING OF OXIDES, NITRIDES, POLYMERS, AND CARBON	
*ION EFFECTS IN OPTICAL FILMS U.J. Gibson	263
*ION BEAM SPUTTER DEPOSITION OF FERROELECTRIC OXIDE THIN FILMS Thomas M. Graettinger, O. Auciello, M.S. Ameen, H.N. Al-Shareef, K. Gifford, and A.I. Kingon	273
PREPARATION OF Bi ₄ Ti ₃ O ₁₂ FILMS BY ECR PLASMA SPUTTERING Hiroshi Masumoto, Takashi Goto, Youichirou Masuda, Akira Baba, and Toshio Hirai	283
DEPOSITION OF ALUMINUM NITRIDE FILM BY ION BEAM ENHANCED REACTIVE MAGNETRON SPUTTERING R.F. Huang, L.S. Wen, H. Wang, J. Wu, and R.J. Hong	289
MODIFICATION OF PROPERTIES OF ION-BEAM-SPUTTERED YTTRIUM-OXIDE THIN FILMS BY LOW-ENERGY ION BOMBARDMENT K.A. Klemm, L.F. Johnson, and M.B. Moran	295
OXIDATION OF AlN-Al ₂ O ₃ COMPOSITE FILM PREPARED BY MICRO-WAVE PLASMA CVD Yoshihiro Someno, Makoto Sasaki, and Toshio Hirai	301
CARBON FILM DEPOSITION ON SILICON USING LOW ENERGY ION BEAMS Qin Fuguang, Yao Zhenyu, Ren Zhizhang, S.-T. Lee, I. Bello, X. Feng, L.J. Huang, and W.M. Lau	307

*Invited Paper

SYNTHESIS OF BORON NITRIDE FILM BY ION BEAM DEPOSITION Z. Xia, G.L. Zhang, and W.L. Lin	315
PACVD FLUORINATED SILICON NITRIDE FILMS DEPOSITED FROM SiF ₄ /NH ₃ GAS MIXTURES A. Castro, M. Gasset, C. Gomez-Aleixandre, O. Sanchez, and J.M. Albella	321
THE ROLE OF DILUTION GAS IN PLASMA DEPOSITION OF AMORPHOUS HYDROGENATED CARBON Hsueh Yi Lu and Mark A. Petrich	327
PART VII: ION PROCESSING OF METALS	
*ION BEAM DEPOSITION OF MULTILAYER MAGNETIC FILMS Masakatsu Senda	335
THIN FILM GROWTH USING LOW-ENERGY MULTI-ION BEAM DEPOSITION SYSTEM S. Shimizu, N. Sasaki, S. Ogata, O. Tsukakoshi, S. Seki, and H. Yamakawa	347
OPTICAL SPECTROSCOPIC PROFILING OF ION BEAM SPUTTERING J.D. Klein and A. Yen	353
THE EFFECTS OF ION ENERGY ON CARBON AND TUNGSTEN FILMS FABRICATED BY DIRECT ION BEAM DEPOSITION AND ION BEAM SPUTTERING DEPOSITION I. Kataoka, K. Ito, N. Hoshi, T. Yonemitsu, K. Etoh, I. Yamada, and Jean-Jacques Delaunay	359
THE INFLUENCE OF ION BOMBARDMENT ON THE SURFACE COMPOSITION OF 70 wt% Cu-30 wt% Zn ALPHA-BRASS Vjekoslav Franetovic	365
PLASMA IMMERSION SURFACE MODIFICATION WITH METAL ION PLASMA I.G. Brown, X. Godechot, and K.M. Yu	371
SELECTIVE COPPER PLATING IN SILICON DIOXIDE TRENCHES WITH METAL PLASMA IMMERSION ION IMPLANTATION Meng-Hsiung Kiang, Carey A. Pico, Michael A. Lieberman, Nathan W. Cheung, X.Y. Qian, and K.M. Yu	377
MAGNETRON-ENHANCED REACTIVE ION-ETCHING OF Al-1%Si- 2%Cu ALLOY C.Y. Fu, R. Hsu, and V. Malba	385
ARGON PLASMA INDUCED SURFACE MODIFICATIONS FOR RESISTLESS PATTERNING OF ALUMINUM FILMS Neeta Agrawal, R.D. Tarey, and K.L. Chopra	389
AUTHOR INDEX	395
SUBJECT INDEX	397

*Invited Paper